

**Amendments to the Claims:**

1. (Currently amended) A test key layout, comprising:

a first test pattern substantially disposed at a center position of a test key area,  
5 wherein said first test pattern consists of a pair of rectangular shaped symmetric patterns having a length L and a width W, and wherein said test key area comprises a reference X-Y coordinate;

a second test pattern arranged in proximity to said first test pattern in 45 degree directions with respect to said first test pattern; and

10 a third test pattern disposed next to said first test pattern along an X axis of said reference X-Y coordinate; and

a fourth test pattern disposed a distance S<sub>1</sub> from said first test pattern along a Y-axis of said reference X-Y coordinate.

15 ~~wherein said first test pattern, said second test pattern, and said third test pattern are arranged like a capital "H" within said test key area.~~

2. (Original) The test key layout of claim 1 wherein said test key layout is made on a photomask comprising an array of deep-trench (DT) capacitor patterns, and wherein said rectangular shaped symmetric patterns have a dimension that is substantial equal to 20 dimension of said DT capacitor patterns.

3. (Original) The test key layout of claim 1 wherein said test key layout is capable of exclusively monitoring 3-foil aberration effect without affected by co-existed COMA aberration effect.

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4. (Canceled)

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5. (Original) The test key layout of claim [[4]]1 wherein  $S_1 = 3L$ .
6. (Original) The test key layout of claim 1 wherein said second test pattern is disposed a distance  $S_2$  from said third test pattern.
7. (Original) The test key layout of claim 6 wherein  $S_2 = L$ .
8. (Original) The test key layout of claim 1 wherein said third test pattern is disposed a distance  $S_3$  from said first test pattern.
9. (Original) The test key layout of claim 8 wherein  $S_3 = W$ .